

# PHP9NQ20T

# N-channel TrenchMOS standard level FET

Rev. 03 — 16 December 2010

**Product data sheet** 

## 1. Product profile

## 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

## 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

## 1.3 Applications

- DC-to-DC converters
- General purpose switching
- Motor control circuits

- Off-line switched-mode power supplies
- TV and computer monitor power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	200	V				
$I_D$	drain current	$T_{mb} = 25  ^{\circ}C;  V_{GS} = 10  V$	-	-	8.7	Α				
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	-	88	W				
Static char	Static characteristics									
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A};$ $T_j = 25 \text{ °C}$	-	300	400	mΩ				
Dynamic c	Dynamic characteristics									
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A};$ $V_{DS} = 160 \text{ V}; T_j = 25 \text{ °C}$	-	12	-	nC				



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow A$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PHP9NQ20T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	200	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	200	V
$V_{GS}$	gate-source voltage		-30	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C	-	6.2	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	-	8.7	Α
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	35	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	88	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	8.7	Α
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	35	Α
Avalanche i	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 7.2 A; $V_{sup}$ ≤ 25 V; unclamped; $t_p$ = 100 $\mu s$ ; $R_{GS}$ = 50 $\Omega$	-	93	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{unclamped}$	-	8.7	Α

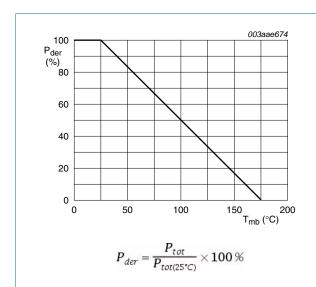


Fig 1. Normalized total power dissipation as a function of mounting base temperature

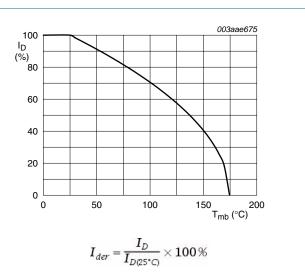


Fig 2. Normalized continuous drain current as a function of mounting base temperature

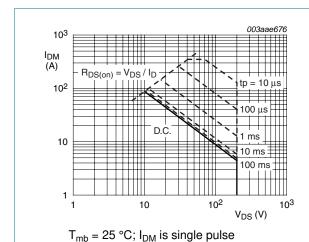


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

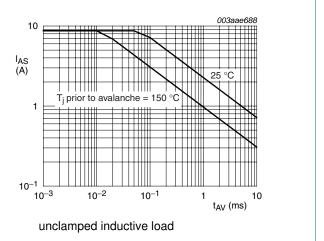


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	-	-	1.7	K/W	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

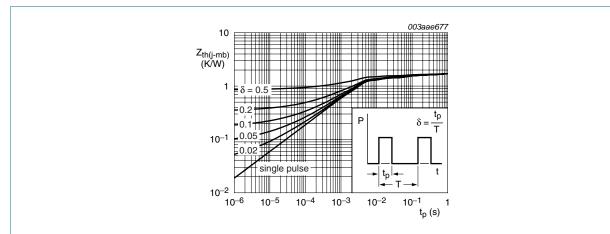


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A}; T_j = 175 \text{ °C}$	-	-	1.16	Ω
	resistance	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$	-	300	400	mΩ
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 9 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}$	-	24	-	nC
Q <sub>GS</sub>	gate-source charge		-	4	-	nC
$Q_{GD}$	gate-drain charge		-	12	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	959	-	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	93	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	54	-	рF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 100 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	19	-	ns
$t_{d(off)}$	turn-off delay time		-	25	-	ns
t <sub>f</sub>	fall time		-	15	-	ns
9 <sub>fs</sub>	transfer conductance	$V_{DS} = 25 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$	3.8	6	-	S
L <sub>D</sub>	internal drain inductance	from drain lead to centre of die ; $T_j = 25$ °C	-	4.5	-	nΗ
		from tab to centre of die ; $T_j = 25$ °C	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 9 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	92	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.5	-	μC

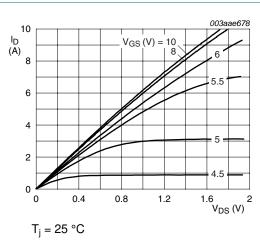


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

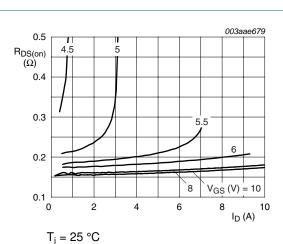


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

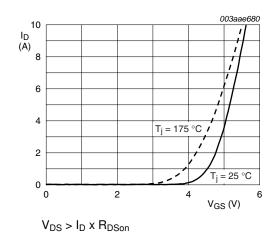


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

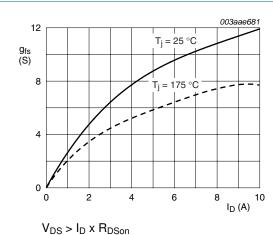


Fig 9. Forward transconductance as a function of drain current; typical values

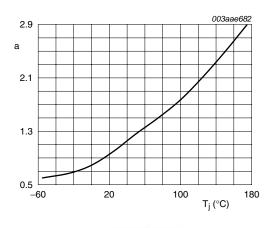
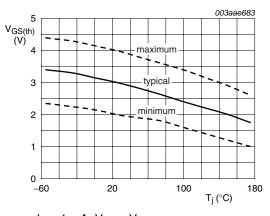


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D=1\ mA;\ V_{DS}=V_{GS}$ 

Fig 11. Gate-source threshold voltage as a function of junction temperature

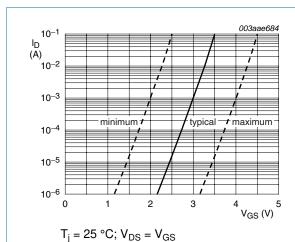
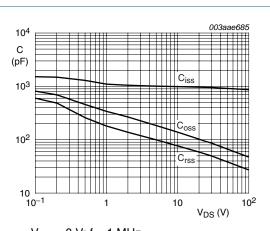


Fig 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

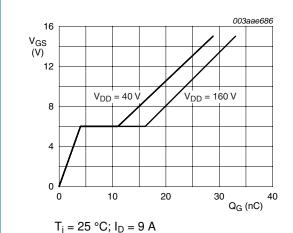
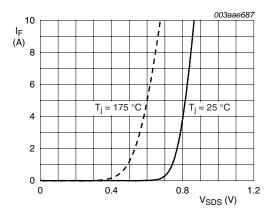


Fig 14. Gate-source voltage as a function of gate charge; typical values

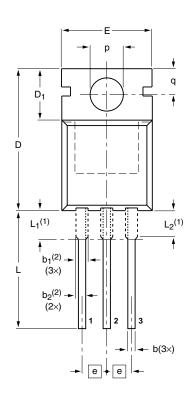


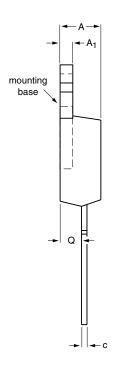
 $V_{GS} = 0 V$ 

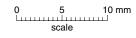
Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78







### DIMENSIONS (mm are the original dimensions)

UNI	T A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q	
mn	n 4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

PHP9NQ20T

**Product data sheet** 

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Nexperia PHP9NQ20T

## N-channel TrenchMOS standard level FET

# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PHP9NQ20T v.3	20101216	Product data sheet	-	PHB_PHD_PHP9NQ20T v.2			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
	<ul> <li>Type number</li> </ul>	er PHP9NQ20T separate	d from data sheet F	PHB_PHD_PHP9NQ20T v.2.			
PHB_PHD_PHP9NQ20T v.2	20001001	Product specification	-	PHB_PHD_PHP9NQ20T v.1			

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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